



N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI®

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
400)/	122mΩ @ V _{GS} = 10V	2.9A
100V	133mΩ @ V_{GS} = 4.5 V	2.7A

Description

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

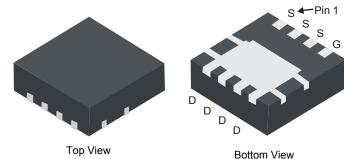
Features

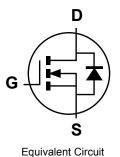
- 100% Unclamped Inductive Switch (UIS) test in production
- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: POWERDI3333
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.034 grams (approximate)

POWERDI3333





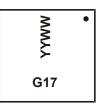
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H170SFG-7	Standard	POWERDI3333	2000/Tape & Reel
DMN10H170SFG-13	Standard	POWERDI3333	3000/Tane & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



G17 = Product marking code YYWW = Date code marking YY = Last digit of year (ex: 10 for 2010) WW = Week code (01 – 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ $T_C = +25^{\circ}C$	I _D	2.9 2.4 8.5	А
	t<10s	T _A = +25°C T _A = +70°C	I _D	3.7 3.0	А
Maximum Continuous Body Diode Forward Curren		I _S	3.0	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	16	Α
Avalanche Current (Note 7)			Iar	5.3	Α
Avalanche Energy (Note 7)			Ear	20	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Davier Dissination (Note 5)	T _A = +25°C	Б	0.94	W	
Total Power Dissipation (Note 5)	T _A = +70°C	P_{D}	0.6	VV	
Thermal Peciatones, Junction to Ambient (Note 5)	Steady State	В	137	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	82	°C/W	
Total Power Dissipation (Note 6)	T _A = +25°C	D	2.0	W	
Total Fower Dissipation (Note o)	T _A = +70°C	P_{D}	1.3		
Thermal Begintance, Junction to Ambient (Note 6)	Steady State	0	60	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	36	°C/W	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	7.0	°C/W	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)				•		
Gate Threshold Voltage	V _{GS(th)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance		_	99	122	mΩ	$V_{GS} = 10V, I_D = 3.3A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	104	133	11122	$V_{GS} = 4.5V, I_D = 3.0A$
Forward Transfer Admittance	Y _{fs}	_	4.4	_	S	$V_{DS} = 10V, I_D = 3.3A$
Diode Forward Voltage	V_{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_S = 3.3A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	870.7	_	pF	.,
Output Capacitance	Coss	_	40.8	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	24.6	_	pF	1 = 1.0WH2
Gate resistance	Rq	_	1.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qq	_	7.0	_	nC	
Total Gate Charge (V _{GS} = 10V)	Qq	_	14.9	_	nC	., 50,4,1, 0,00
Gate-Source Charge	Qgs	_	3.3	_	nC	$V_{DS} = 50V, I_D = 3.3A$
Gate-Drain Charge	Q_{gd}	_	3.0	_	nC	7
Turn-On Delay Time	t _{D(on)}	_	4.4	_	ns	
Turn-On Rise Time	tr	_	2.3	_	ns	V _{DD} = 50V, V _{GEN} = 10V,
Turn-Off Delay Time	t _{D(off)}	_	13.9	_	ns	$R_{GEN} = 6.0\Omega$, $I_D = 3.3A$
Turn-Off Fall Time	t _f	_	3.4	_	ns	
Reverse Recovery Time	t _{rr}	_	22.4	_	ns	
Reverse Recovery Charge	Q _{rr}	_	19.7	_	nC	$I_S = 3.3A$, dl/dt = 100A/ μ s

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

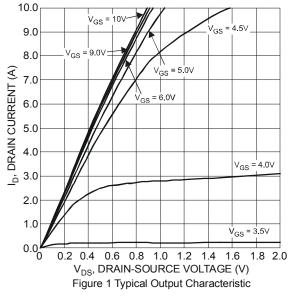
7. UIS in production with L = 1.43mH, T_J = +25°C.

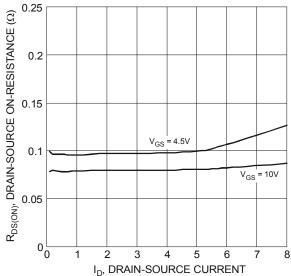
^{8.} Short duration pulse test used to minimize self-heating effect.

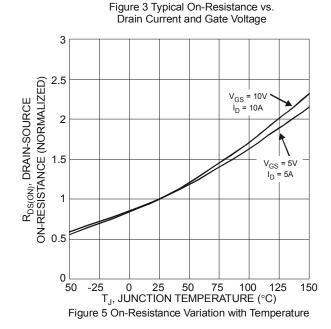
^{9.} Guaranteed by design. Not subject to product testing.











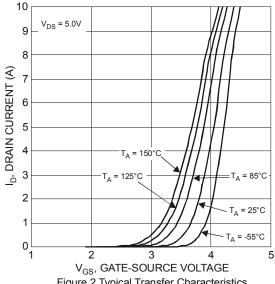


Figure 2 Typical Transfer Characteristics

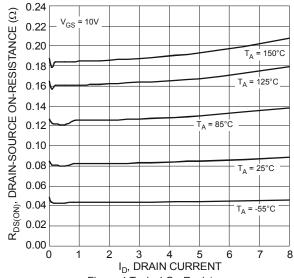


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

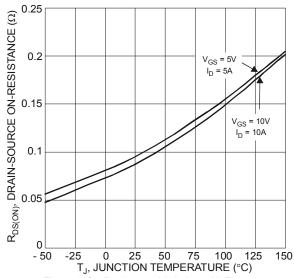


Figure 6 On-Resistance Variation with Temperature





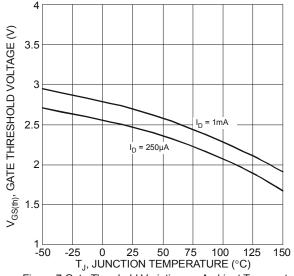
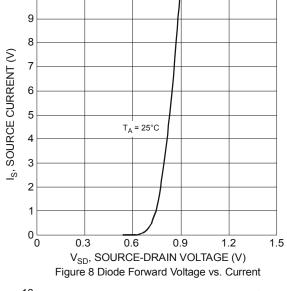
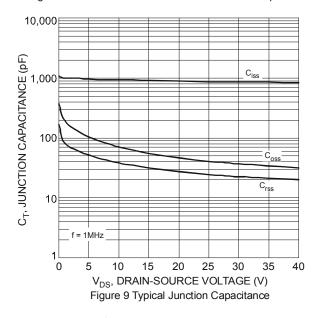
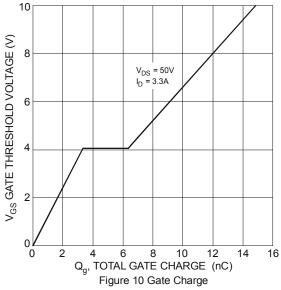


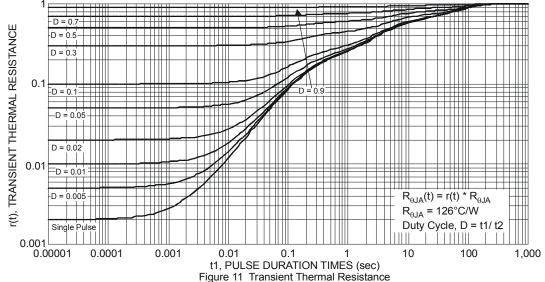
Figure 7 Gate Threshold Variation vs. Ambient Temperature



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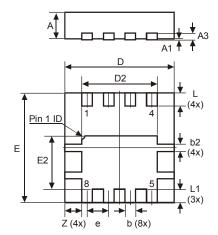






Package Outline Dimensions

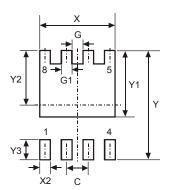
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
Е	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A1	0	0.05	0.02		
А3	_	_	0.203		
b	0.27	0.37	0.32		
b2	_	_	0.20		
L	0.35	0.45	0.40		
L1	_	_	0.39		
е	_	_	0.65		
Z	_	-	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.650			
G	0.230			
G1	0.420			
Y	3.700			
Y1	2.250			
Y2	1.850			
Y3	0.700			
Х	2.370			
¥2	0.420			



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